4-Bit Dual-Supply Non-Inverting Level Translator

The NLSV4T3144 is a 4-bit configurable dual-supply bus buffer level translator. The input (IN_x_n) and output (OUT_x_n) ports are designed to track two different power supply rails, $V_{\rm CCA}$ and $V_{\rm CCB}$ respectively. Both supply rails are configurable from 1.6 V to 3.6 V allowing low–voltage translation from the input to the output port.

Features

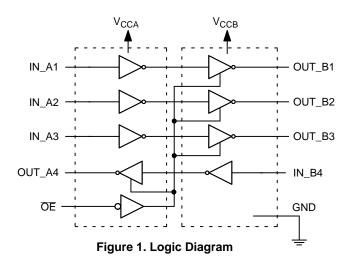
- Wide V_{CCA} and V_{CCB} Operating Range: 1.6 V to 3.6 V
- High-Speed w/ Balanced Propagation Delay
- Inputs and Outputs have OVT Protection to 5.5 V
- Outputs at 3-State until Active V_{CCA} and V_{CCB} are Reached
- Power-Off Protection
- Ultra-Small Packaging: 1.7 mm x 2.0 mm UQFN-12
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

Typical Applications

- Mobile Phones, PDAs, Other Portable Devices
- SPI™ Bus Voltage Translation

Important Information

 ESD Protection for All Pins: HBM (Human Body Model) > 3000 V





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MARKING DIAGRAM



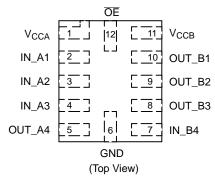
WG = Specific Device Code

M = Date Code

= Pb-Free Package

(Note: Microdot may be in either location)

PIN ASSIGNMENTS



ORDERING INFORMATION

Device	Package	Shipping [†]
NLSV4T3144MUTAG	UQFN-12 (Pb-Free)	3000/Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

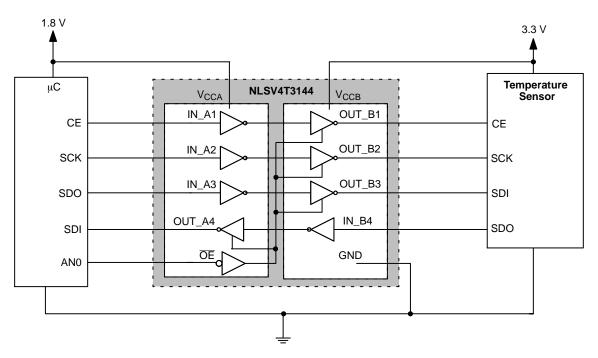


Figure 2. Typical Application: SPI Bus Voltage Translator

PIN NAMES

	1
Pins	Description
V _{CCA}	'A' DC Power Supply
V _{CCB}	'B' DC Power Supply
GND	Ground
IN_A1, IN_A2, IN_A3	Input (Referenced to V _{CCA})
IN_B4	Input (Referenced to V _{CCB})
OUT_B1, OUT_B2, OUT_B3	Output (Referenced to V _{CCB})
OUT_A4	Output (Referenced to V _{CCA})
ŌĒ	Output Enable (Referenced to V _{CCA})

TRUTH TABLE

	Inputs	Outputs
ŌĒ	IN_A1, IN_A2, IN_A3, IN_B4	OUT_B1, OUT_B2, OUT_B3, OUT_A4
Н	Х	3-State
L	L	L
	Н	Н

MAXIMUM RATINGS

Symbol	Parameter	Value	Condition	Unit
V _{CCA} , V _{CCB}	DC Supply Voltage, V _{CCA} ≤ V _{CCB}	-0.5 to +5.5		V
VI	DC Input Voltage IN_x _n	-0.5 to +5.5		V
V _C	Control Input OE	-0.5 to +5.5		V
Vo	DC Output Voltage (Power Down) OUT_x _n	-0.5 to +5.5	$V_{CCA} = V_{CCB} = 0$	V
	(Active Mode) OUT_x _n	-0.5 to +5.5		
	(Tri–State Mode) OUT_x _n	-0.5 to +5.5		
I _{IK}	DC Input Diode Current	-20	V _I < GND	mA
I _{OK}	DC Output Diode Current	-50	V _O < GND	mA
Io	DC Output Source/Sink Current	±50		mA
I _{CCA} , I _{CCB}	DC Supply Current Per Supply Pin	±100		mA
I _{GND}	DC Ground Current per Ground Pin	±100		mA
T _{STG}	Storage Temperature	-65 to +150		°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V _{CCA} , V _{CCB}	Positive DC Supply Voltage, V _{CCA} ≤ V _{CCB}	1.6	3.6	V
VI	Bus Input Voltage	GND	3.6	V
V _C	Control Input OE	GND	3.6	V
V _{IO}	DC Output Voltage (Power Down) OUT_x _n	GND	3.6	V
	(Active Mode) OUT_x _n			
	(Tri–State Mode) OUT_x _n			
T _A	Operating Temperature Range	-40	+85	°C
Δt / ΔV	Input Transition Rise or Rate V _I , from 30% to 70% of V _{CCA} and V _{CCB} ; V _{CCA} = V _{CCB} = 3.3 V \pm 0.3 V	0	10	ns

DC ELECTRICAL CHARACTERISTICS

					−40°C to	o + 85°C]
Symbol	Parameter	Test Conditions	V _{CCA} (V)	V _{CCB} (V)	Min	Max	Unit
V _{IH}	Input HIGH Voltage		2.7 – 3.6	≥ V _{CCA}	2.0	-	V
(IN_A1, IN_A2,			2.3 – 2.7	1	1.6	_	
IN_A3, \overline{OE}			1.6 –2.3	1	0.65 * V _{CCA}	-	
V _{IH}	Input HIGH Voltage		≤ V _{CCB}	2.7 – 3.6	2.0	-	V
(IN_B4)	N_B4)			2.3 – 2.7	1.6	-	
				1.6 –2.3	0.65 * V _{CCB}	-	
V_{IL}	Input LOW Voltage		2.7 – 3.6	≥ V _{CCA}	_	0.8	V
(IN_A1, IN_A2,			2.3 – 2.7		_	0.7	
IN_A3, OE)			1.6 –2.3		-	0.35 * V _{CCA}	
V_{IL}	Input LOW Voltage		≤ V _{CCB}	2.7 – 3.6	_	0.8	V
(IN_B4)				2.3 – 2.7	-	0.7	
				1.6 –2.3	_	0.35 * V _{CCB}	
V _{OH}	Output HIGH Voltage	$I_{OH} = -100 \mu A; V_I = V_{IH}$	≤ V _{CCB}	1.6 – 3.6	V _{CCB} - 0.2	_	V
(OUT_B1, OUT_B2,		$I_{OH} = -6 \text{ mA}; V_I = V_{IH}$	1.6	1.6	1.25	-	
OUT_B3)			2.3	2.3	2.0	-	
		$I_{OH} = -12 \text{ mA}; V_I = V_{IH}$	2.3	2.3	1.8	-	
			2.7	2.7	2.2	-	
		$I_{OH} = -18 \text{ mA}; V_I = V_{IH}$	2.3	2.3	1.7	-	
			3.0	3.0	2.4	-	
		$I_{OH} = -24 \text{ mA}; V_I = V_{IH}$	3.0	3.0	2.2	-	
V _{OH}	Output HIGH Voltage	$I_{OH} = -100 \mu A; V_I = V_{IH}$	1.6 – 3.6	≥ V _{CCA}	V _{CCA} - 0.2	-	V
(OUT_A4)		$I_{OH} = -6 \text{ mA}; V_I = V_{IH}$	1.6	1.6	1.25	-	
			2.3	2.3	2.0	-	
		$I_{OH} = -12 \text{ mA}; V_I = V_{IH}$	2.3	2.3	1.8	-	
			2.7	2.7	2.2	-	
		$I_{OH} = -18 \text{ mA}; V_I = V_{IH}$	2.3	2.3	1.7	-	
			3.0	3.0	2.4	-	
		$I_{OH} = -24 \text{ mA}; V_I = V_{IH}$	3.0	3.0	2.2	-	
V _{OL}	Output LOW Voltage	$I_{OL} = 100 \mu A; V_I = V_{IH}$	≤ V _{CCB}	1.6 – 3.6	-	0.2	V
(OUT_B1, OUT_B2,		$I_{OL} = 6 \text{ mA}; V_I = V_{IH}$	1.6	1.6	_	0.3	
OUT_B3)		I_{OL} = 12 mA; V_I = V_{IH}	2.3	2.3	-	0.4	
			2.7	2.7	-	0.4	
		I_{OL} = 18 mA; V_I = V_{IH}	2.3	2.3	_	0.6	
			3.0	3.0	_	0.5	
		I_{OL} = 24 mA; V_I = V_{IH}	3.0	3.0	-	0.6	
V _{OL}	Output LOW Voltage	$I_{OL} = 100 \mu A; V_I = V_{IH}$	1.6 – 3.6	≥ V _{CCA}	-	0.2	V
(OUT_A4)		$I_{OL} = 6 \text{ mA}; V_I = V_{IH}$	1.6	1.6	_	0.3	
		I_{OL} = 12 mA; V_I = V_{IH}	2.3	2.3	-	0.4	
			2.7	2.7	-	0.4	
		I _{OL} = 18 mA; V _I = V _{IH}	2.3	2.3	-	0.6	
			3.0	3.0	-	0.5	
		I _{OL} = 24 mA; V _I = V _{IH}	3.0	3.0	_	0.6	1

DC ELECTRICAL CHARACTERISTICS

					−40°C to	o + 85°C	
Symbol	Parameter	Test Conditions	V _{CCA} (V)	V _{CCB} (V)	Min	Max	Unit
I _{IN}	Input Leakage Current	$V_{IN_A1} = V_{IN_A2} = V_{IN_A3} = V_{CCA} \text{ or GND;}$ $V_{IN_B4} = V_{CCB} \text{ or GND}$	≤ V _{CCB}	1.6 – 3.6	-1.0	+1.0	μΑ
l _{OZ}	I/O Tri – State Output Leakage Current	TA = 25°C, $\overline{\text{OE}}$ = V _{CCA}	≤ V _{CCB}	1.6 – 3.6	-	1.0	μΑ
I _{CCA}	Quiescent Supply Current	$V_{IN_A1} = V_{IN_A2} = V_{IN_A3} = V_{CCA}$ or GND; $V_{IN_B4} = V_{CCB}$ or GND $\overline{OE} = \text{GND}, I_O = 0$	≤ V _{CCB}	1.6 – 3.6	-	3.0	μΑ
Іссв	Quiescent Supply Current	$\begin{split} &V_{IN_A1} = V_{IN_A2} = \ V_{IN_A3} = \\ &V_{CCA} \text{ or GND;} \\ &V_{IN_B4} = V_{CCB} \text{ or GND} \\ &\overline{OE} = \text{GND, I}_O = 0 \end{split}$	≤ V _{CCB}	1.6 – 3.6	-	3.0	μΑ
I _{CCA} + I _{CCB}	Quiescent Supply Current	$\begin{split} &V_{IN_A1} = V_{IN_A2} = \ V_{IN_A3} = \\ &V_{CCA} \text{ or GND;} \\ &V_{IN_B4} = V_{CCB} \text{ or GND} \\ &\overline{OE} = \text{GND, I}_O = 0 \end{split}$	≤ V _{CCB}	1.6 – 3.6	-	6.0	μΑ

NOTE: Connect ground before applying supply voltage V_{CCA} or V_{CCB}. This device is designed with the feature that the power–up sequence of V_{CCA} and V_{CCB} will not damage the IC.

AC ELECTRICAL CHARACTERISTICS

					-40°C t	o +85°C			
					V _{CC}	_B (V)			
			3	.6	2	.8	1	.6	1
Symbol	Parameter	V _{CCA} (V)	Min	Max	Min	Max	Min	Max	Unit
t _{PLH} , t _{PHL}	Propagation	3.6		3					ns
	Delay,	2.8		3.1		3.3			1
İ	Input to Output	1.6		4.3		4.5		6.1	1
t _{PZH} , t _{PZL}	Output Enable,	3.6		8.7					ns
	OE to Output	2.8		10.3		10.7			1
		1.6		17.2		18		20	1
t _{PHZ} , t _{PLZ}	Output	3.6		7.8					ns
	Disable,	2.8		8.2		8.4			1
	OE to Output	1.6		9.5		9.8		10.5	1
t _{OSHL} ,	Output to Output Skew	3.6		0.25		•			ns
toslh		2.8		0.25		0.25			1
		1.6		0.25		0.25		0.25	1

NOTE: Propagation delays defined per Figure 3.

CAPACITANCE

Symbol	Parameter	Test Conditions	Typ (Note 1)	Unit
C _I	Control Pin (OE) Input Capacitance	$V_{CCA} = V_{CCB} = 3.3 \text{ V}, V_I = 0 \text{ V or } V_{CCA/B}$	3.5	pF
C _{IN}	Input Pin Capacitance	$V_{CCA} = V_{CCB} = 3.3 \text{ V}, V_I = 0 \text{ V or } V_{CCA/B}$	5.0	pF
C _{OUT}	Output Pin Capacitance	$V_{CCA} = V_{CCB} = 3.3 \text{ V}, V_I = 0 \text{ V or } V_{CCA/B}$	5.0	pF
C _{PD}	Power Dissipation Capacitance	$V_{CCA} = V_{CC2} = 3.3 \text{ V}, V_{I} = 0 \text{ V or } 3.3 \text{ V}, f = 10 \text{ MHz}$	10	pF

^{1.} Typical values are at $T_A = +25^{\circ}C$.

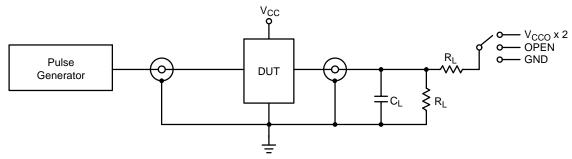


Figure 3. AC (Propagation Delay) Test Circuit

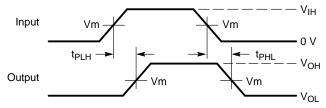
Test	Switch
t _{PLH} , t _{PHL}	OPEN
t _{PLZ} , t _{PZL}	V _{CCO} x 2 at V _{CCO} = 3.0 V – 3.6 V, 2.3 V – 2.7 V, 1.65 V – 1.95 V, 1.4 V – 1.6 V
t _{PHZ} , t _{PZH}	GND

C_L = 15 pF or equivalent (includes probe and jig capacitance)

 $R_L = 2 k\Omega$ or equivalent

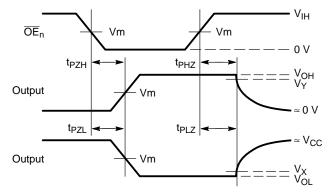
 Z_{OUT} of pulse generator = 50 Ω

 $\ensuremath{\text{V}_{\text{CCO}}}$ is the supply voltage referenced to by the output being tested



Waveform 1 - Propagation Delays

 $t_R = t_F = 2.0 \text{ ns}, 10\% \text{ to } 90\%; f = 1 \text{ MHz}; t_W = 500 \text{ ns}$



Waveform 2 – Output Enable and Disable Times $t_R = t_F = 2.0 \text{ ns}$, 10% to 90%; f = 1 MHz; $t_W = 500 \text{ ns}$

Figure 4. AC (Propagation Delay) Test Circuit Waveforms

Symbol	Input Pin Output Pin
V _m	V _{CCX} /2
V _X	V _{OL} x 0.1
V _Y	V _{OH} x 0.9

UQFN12 1.7x2.0, 0.4P CASE 523AE-01 **ISSUE A**

DATE 11 JUN 2007



PIN 1 REFERENCE

0.10 C

0.10 С

0.05 С

0.05 C **TOP VIEW**

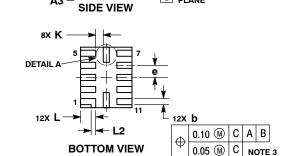
A1

2X |

12X 🗀



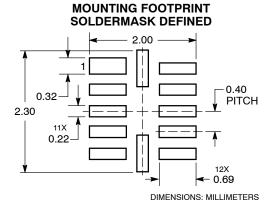




DETAIL B

SEATING PLANE

-A B



NOTES:

- DIMENSIONING AND TOLERANCING PER ASME
- Y14.5M, 1994. CONTROLLING DIMENSION: MILLIMETERS
- DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.30 MM
- FROM TERMINAL TIP.

 MOLD FLASH ALLOWED ON TERMINALS

 ALONG EDGE OF PACKAGE. FLASH 0.03

 MAX ON BOTTOM SURFACE OF
- TERMINALS.
 DETAIL A SHOWS OPTIONAL
 CONSTRUCTION FOR TERMINALS.

	MILLIMETERS			
DIM	MIN	MAX		
Α	0.45	0.55		
A1	0.00	0.05		
A3	0.127	REF		
b	0.15	0.25		
D	1.70	BSC		
E	2.00	BSC		
е	0.40	BSC		
K	0.20			
L	0.45	0.55		
L1	0.00	0.03		
L2	0.15	REF		

GENERIC MARKING DIAGRAM*



XX = Specific Device Code

= Date Code

= Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

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